

# SMD Schottky Barrier Diode

**COMCHIP**  
SMD Diodes Specialist

## CDBF70 (RoHs Device)

**I<sub>o</sub> = 70 mA**

**V<sub>R</sub> = 70 Volts**



### Features

Low forward Voltage.

Designed for mounting on small surface.

Extremely thin / leadless package.

Majority carrier conduction.

### Mechanical data

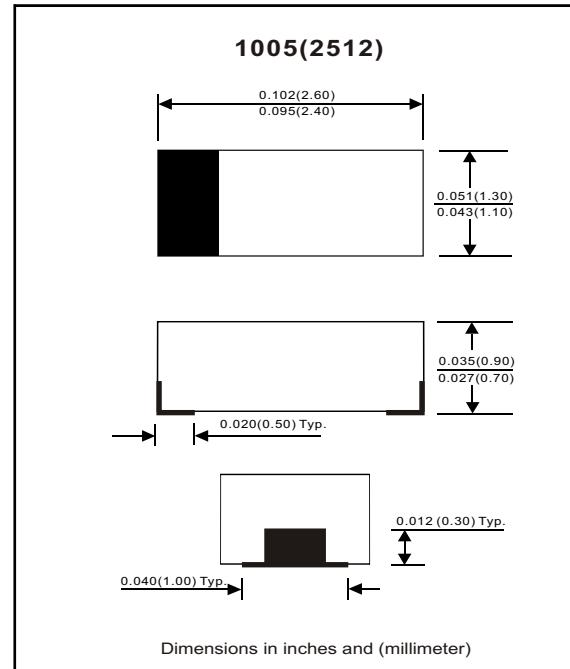
Case: 1005(2512) standard package,  
molded plastic.

Terminals: Gold plated, solderable per  
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.006 gram(approx.).



### Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Peak reverse voltage		V <sub>RM</sub>			70	V
Reverse voltage		V <sub>R</sub>			70	V
RMS reverse voltage		V <sub>R</sub> (RMS)			49	V
Average forward rectified current		I <sub>o</sub>			70	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I <sub>FSM</sub>			0.1	A
Power dissipation		P <sub>D</sub>			200	mW
Storage temperature		T <sub>STG</sub>	-65		+125	°C
Junction temperature		T <sub>j</sub>			+125	°C

### Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 1mA I <sub>F</sub> = 15mA	V <sub>F</sub>			0.41 1	V
Reverse current	V <sub>R</sub> = 50V	I <sub>R</sub>			0.1	uA
Capacitance between terminals	f = 1 MHz, and 0 VDC reverse voltage	C <sub>T</sub>			2	pF
Reverse recovery time	I <sub>F</sub> =I <sub>R</sub> =10mA,I <sub>rr</sub> =0.1xI <sub>R</sub> ,RL=100 Ohm	T <sub>rr</sub>			5	nS

## RATING AND CHARACTERISTIC CURVES (CDBF70)

Fig. 1 - Forward characteristics

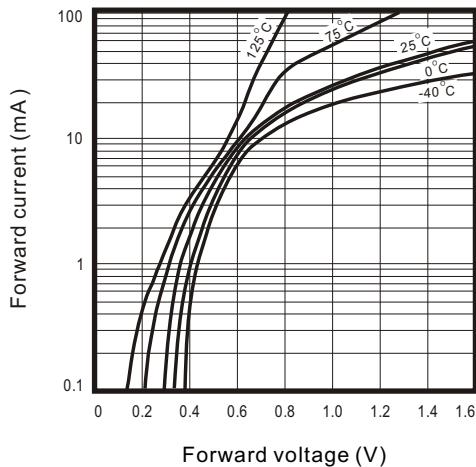


Fig. 2 - Reverse characteristics

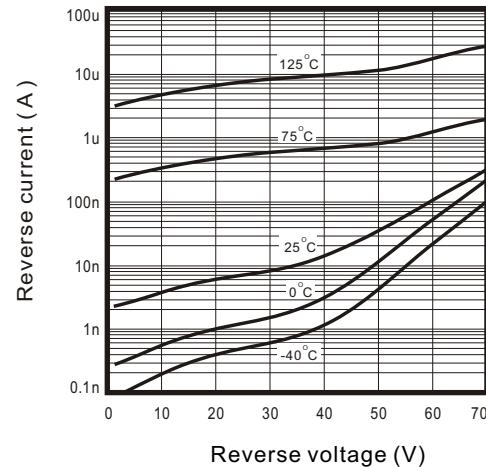


Fig.3 - Capacitance between terminals characteristics

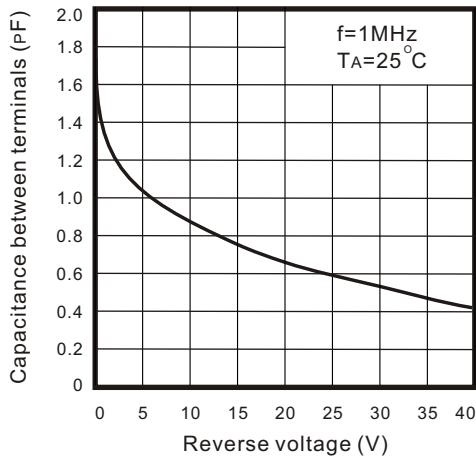


Fig.4 - Current derating curve

